

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (currently amended) A method for repairing a photomask by removing a residual defect in the photomask, the method comprising removing the defect area by gallium chelation with a water-soluble amine polymer containing carboxyl, hydroxyl and amine groups.
2. (original) The method as recited in claim 1, wherein said defect is causative of a partial deterioration in light transmittance of the photomask in its gallium-implanted defect area and an area around the gallium-implanted defect area to restore the light transmittance of said areas in the photomask.
3. (original) The method as recited in claim 1, wherein, in the repair of the photomask, assist gas enhances the etching simultaneously with the focused ion beam irradiation.
4. (original) The method as recited in claim 1, wherein the photomask is a phase shift photomask.
5. (original) The method as recited in claim 1, wherein the pH of the defect area to be treated is about 1-6.
6. (original) The method as recited in claim 5, wherein the pH of the defect area to be treated is about 4.
7. (original) The method as recited in claim 1, wherein the molecular weight of the water-soluble amine polymer is about 23,000.